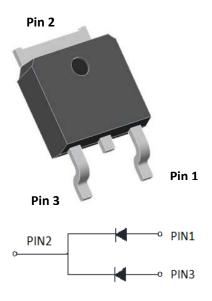


MBR2045CD





Schottky Diodes

Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

• Package: TO-252

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant

 Terminals: Tin plated leads, solderable per J-STD-002 and JESD22-B102

Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR2045CD
Device marking code			MBR2045CD
Repetitive Peak Reverse Voltage	VRRM	V	45
Average Rectified Output Current @60Hz sine wave, R-load, T _C =87°C	Ю	Α	20
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Ta=25°C	IFSM	Α	130
Current Squared Time @1ms≤t≤8.3ms Tj=25°C,	l ² t	A ² s	70
Storage Temperature	T _{stg}	°C	-55 ~ + 150
Junction Temperature	Tj	°C	-55 ~ +1 50

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR2045CD
Maximum instantaneous forward voltage drop per diode	VFM	V	IFM=10.0A	0.63
Maximum DC reverse current at rated DC blocking voltage per diode	IRRM1	mA	VRM=VRRM T _a =25°C	0.2
	IRRM2		VRM=VRRM T _a =125°C	100

Note1:Pulse test:300uS pulse widh,1% duty cycle

Note2:Pulse test:pulse widh 40mS

MBR2045CD

Thermal Characteristics $(T_a=25^{\circ}\mathbb{C} \text{ Unless otherwise specified})$

PARAMETER		SYMBOL	UNIT	MBR2045CD
Thermal Resistance	Between junction and case	R ₀ J-C	°CW	5.0

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR2045CD	Approximate 0.32	2500	2500	25000	Reel

Peak Forward Surge Current (A)

20

■Characteristics (Typical)

FIG1:lo -Tc Curve Average Forward Output Current (A) 28.0 24.0 20.0 16.0 TC measure point 12.0 8.0 4.0 0 150 0 50 100 Case Temperature (℃)

140
120
100
8.3ms Single
Half Sine-Wave
JEDEC Method
60
40

FIG2:Surge Forward Current Capability

FIG3: Forward Voltage

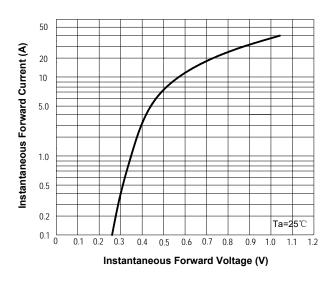
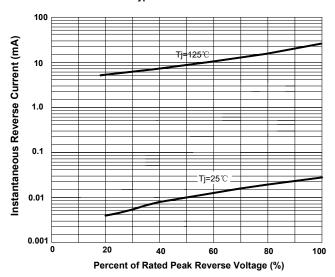


FIG.4: Typical Reverse Characteristics

Number of Cycles

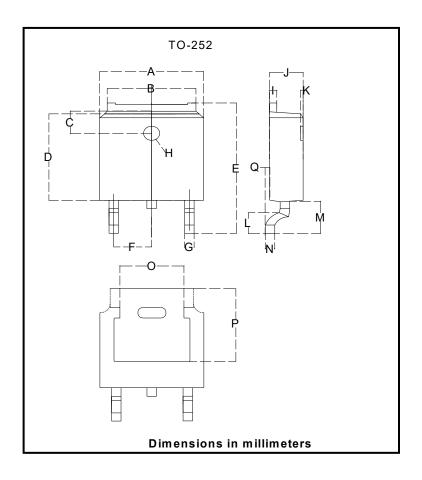
50

100



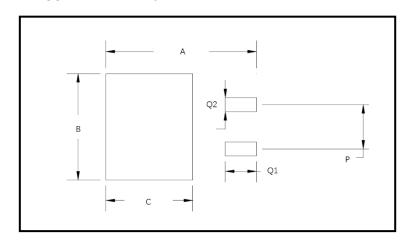


■Outline Dimensions



TO-252				
Dim	Min	Max		
Α	6.500	6.700		
В	5.100	5.460		
С	1.400	1.800		
D	6.000	6.200		
E	10.000	10.400		
F	2.166	2.366		
G	0.660	0.860		
Н	Ф1.050	Ф1.350		
ı	0.460	0.580		
J	2.200	2.400		
K	0	0.300		
L	0.890	2.290		
М	2.730	3.080		
N	0.430	0.580		
0	4.20	4.95		
Р	5.15	5.45		
Q	0	0.2		

■ Suggested Pad Layout



Dim	Millimeters		
Α	11.4		
В	6.74		
С	6.23		
Р	4.56		
Q1	2.28		
Q2	1.52		



MBR2045CD

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